

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Jerome M. Eldridge et al.	Examiner:	Unknown
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	1303.063US2
Title:	GRADED COMPOSITION METAL OXIDE TUNNEL BARRIER INTERPOLY INSULATORS		

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Commissioner for Patents
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In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 10/177096, filed on June 21, 2002, which is relied upon for an earlier filing date under 35 U.S.C. §120.

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Serial No :Unknown

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

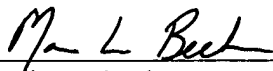
Respectfully submitted,

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First Named Inventor	Eldridge, Jerome
Group Art Unit	Unknown
Examiner Name	Unknown

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Application Number Unknown**Filing Date** Even Date Herewith**First Named Inventor** Eldridge, Jerome**Group Art Unit** Unknown**Examiner Name** Unknown

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Attorney Docket No: 1303.063US2

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number Unknown

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First Named Inventor Eldridge, Jerome

Group Art Unit Unknown

Examiner Name Unknown

Sheet 3 of 6

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached